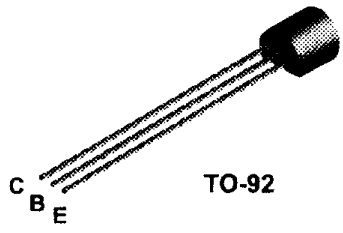
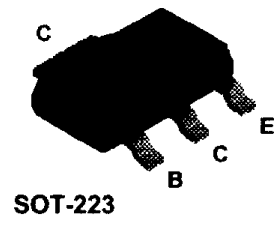


2N7052
2N7053



NZT7053



NPN Darlington Transistor

This device is designed for applications requiring extremely high gain at collector currents to 1.0 A and high breakdown voltage. Sourced from Process 06.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	100	V
V _{CB0}	Collector-Base Voltage	100	V
V _{EB0}	Emitter-Base Voltage	12	V
I _C	Collector Current - Continuous	1.5	A
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		2N7053	*NZT7053	
P _D	Total Device Dissipation	625	1,000	mW
	Derate above 25°C	5.0	8.0	mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	83.3		°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	200	125	°C/W

* Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm².

NPN Darlington Transistor

(continued)

2N7052 / 2N7053 / NZT7053

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHARACTERISTICS					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	100		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100 \mu\text{A}, I_E = 0$	100		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 1.0 \text{ mA}, I_C = 0$	12		V
I_{CBO}	Collector-Cutoff Current	$V_{CB} = 80 \text{ V}, I_E = 0$		0.1	μA
I_{CES}	Collector-Cutoff Current	$V_{CE} = 80 \text{ V}, I_E = 0$		0.2	μA
I_{EBO}	Emitter-Cutoff Current	$V_{EB} = 7.0 \text{ V}, I_C = 0$		0.1	μA

ON CHARACTERISTICS*

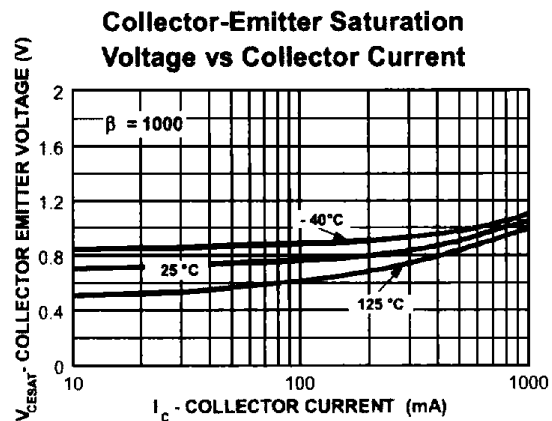
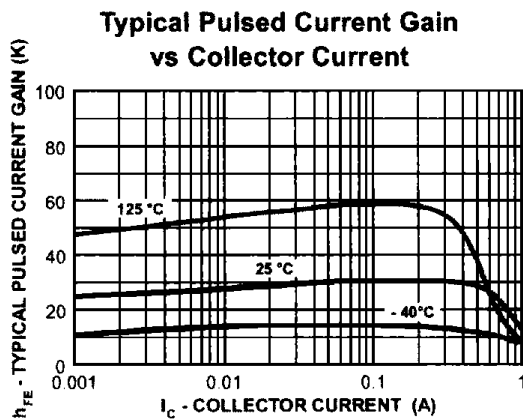
h_{FE}	DC Current Gain	$I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_C = 1.0 \text{ A}, V_{CE} = 5.0 \text{ V}$	10,000 1,000	20,000	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 100 \text{ mA}, I_B = 0.1 \text{ mA}$		1.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = 100 \text{ mA}, V_{BE} = 5.0 \text{ V}$		2.0	V

SMALL SIGNAL CHARACTERISTICS

F_T	Transition Frequency	$I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$	200		MHz
C_{cb}	Collector-Base Capacitance	$V_{CB} = 10 \text{ V}, f = 1.0 \text{ MHz}$ 2N7052 2N7053		10 8.0	pF

*Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 1.0\%$

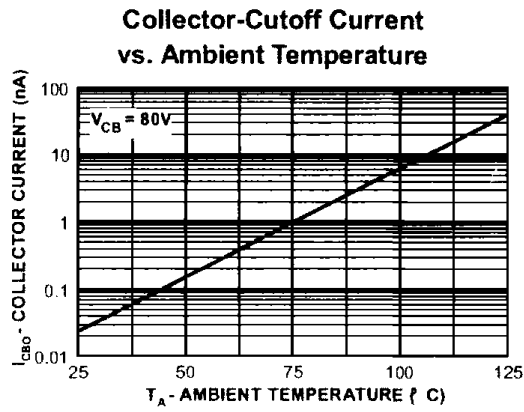
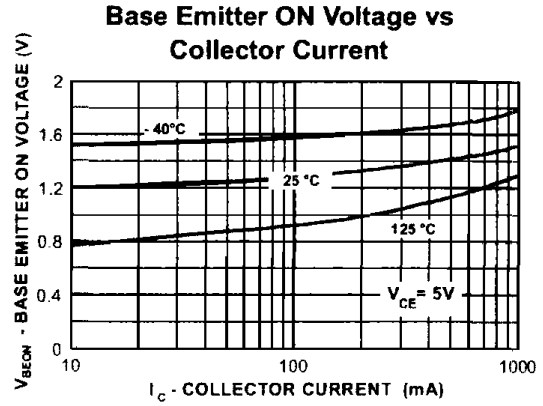
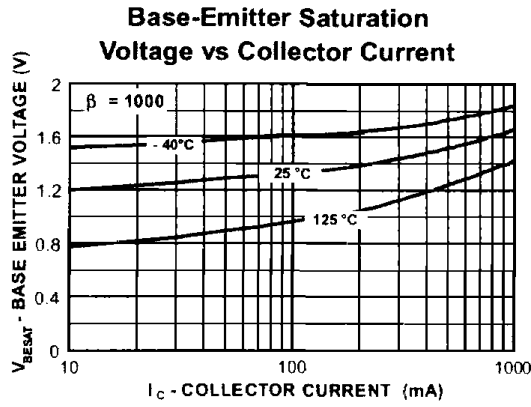
DC Typical Characteristics



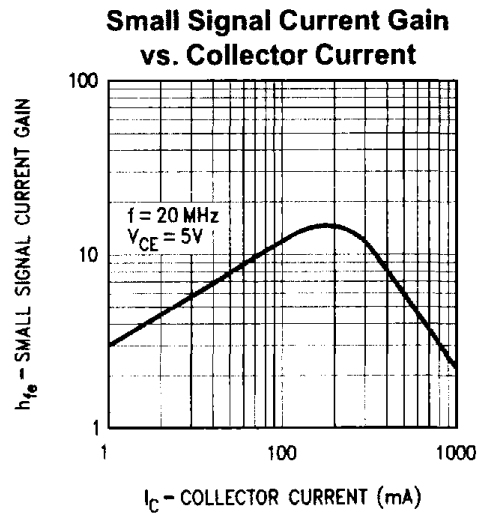
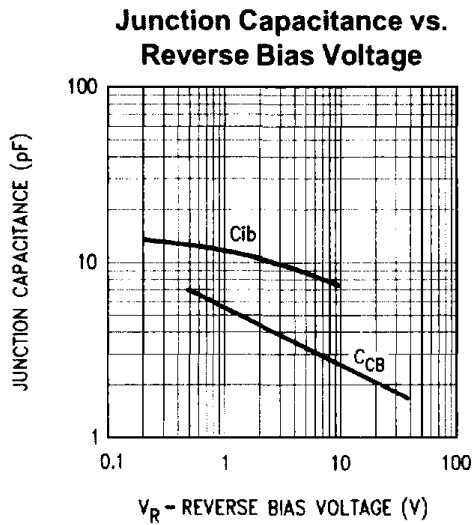
NPN Darlington Transistor

(continued)

DC Typical Characteristics (continued)

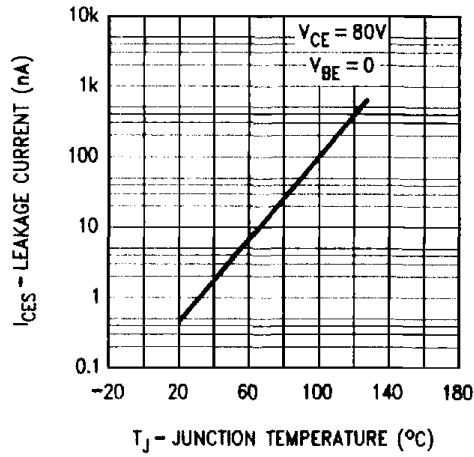


AC Typical Characteristics



AC Typical Characteristics (continued)

Typical Collector-Emitter Leakage Current vs. Temperature



POWER DISSIPATION vs AMBIENT TEMPERATURE

